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Hardware Documentation

Data Sheet

HAL[®] 1002

Highly Precise Programmable Hall-Effect Switch

Edition April 25, 2014 DSH000163_001E

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HAL 1002

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Highly Precise Programmable Hall-Effect Switch

Release Note: Revision bars indicate significant changes to the previous edition.

1. Introduction

The HAL1002 is the improved successor of the HAL1000 Hall switch. The major sensor characteristics, the two switching points B_{ON} and B_{OFF} , are programmable for the application. The sensor can be programmed to be unipolar or latching, sensitive to the magnetic north pole or sensitive to the south pole, with normal or with an electrically inverted output signal. Several examples are shown in Fig. 3–4 through Fig. 3–7.

The HAL1002 is based on the HAL83x family and features a temperature-compensated Hall plate with choppered offset compensation, an A/D converter, digital signal processing, a push-pull output stage, an EEPROM memory with redundancy and lock function for the calibration data, a serial interface for programming the EEPROM, and protection devices at all pins. Internal digital signal processing is of great benefit because analog offsets, temperature shifts, and mechanical stress effects do not degrade the sensor accuracy.

The HAL1002 is programmable by modulating the supply voltage. No additional programming pin is needed. Programming is simplified through the use of a 2-point calibration. Calibration is accomplished by adjusting the sensor output directly to the input signal. Individual adjustment of each sensor during the customer's manufacturing process is possible. With this calibration procedure, the tolerances of the sensor, the magnet, and the mechanical positioning can be compensated for the final assembly. This offers a low-cost alternative for all applications that presently require mechanical adjustment or other system calibration.

In addition, the temperature compensation of the Hall IC can be tailored to all common magnetic materials by programming first and second order temperature coefficients of the Hall sensor sensitivity. This enables operation over the full temperature range with constant switching points.

The calculation of the individual sensor characteristics and the programming of the EEPROM memory can easily be done with a PC and the application kit from Micronas.

The sensor is designed and produced in sub-micron CMOS technology for the use in hostile industrial and automotive applications with nominal supply voltage of 5 V in the ambient temperature range from -40 °C up to 150 °C.

The HAL1002 is available in the leaded package TO92UT-2.

1.1. Major Applications

Due to the sensor's versatile programming characteristics, the HAL1002 is the optimal system solution for applications which require very precise contactless switching:

- Endpoint detection
- Level switch (e.g. liquid level)
- Electronic fuse (current measurement)

1.2. Features

- High-precision Hall switch with programmable switching points and switching behavior
- AEC-Q100 qualified
- EMC and ESD optimized design ESD HBM performance >7 kV
- Switching points programmable from –150 mT up to 150 mT in steps of 0.5% of the magnetic field range
- Multiple programmable magnetic characteristics in a non-volatile memory (EEPROM) with redundancy and lock function
- Temperature characteristics are programmable for matching all common magnetic materials
- Programming through a modulation of the supply voltage
- Operates from –40 °C up to 150 °C ambient temperature
- Operates from 4.5 V up to 8.5 V supply voltage in specification and functions up to 11 V
 - Operates with static magnetic fields and dynamic magnetic fields up to 2 kHz
 - Magnetic characteristics are extremely robust against mechanical stress effects
 - Overvoltage and reverse-voltage protection at all pins
 - Short-circuit protected push-pull output

2. Ordering Information

2.1. Marking Code

The HAL1002 has a marking on the package surface (branded side). This marking includes the name of the sensor and the temperature range.

Туре	Temperature Range		
	Α		
HAL1002	1002A		

2.2. Operating Junction Temperature Range (T_J)

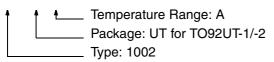
The Hall sensors from Micronas are specified to the chip temperature (junction temperature T_J).

A: $T_J = -40 \ ^{\circ}C \text{ to } +170 \ ^{\circ}C$

The relationship between ambient temperature (T_A) and junction temperature is explained in Section 5.3. on page 21.

2.3. Hall Sensor Package Codes

HALXXXXPA-T



Example: HAL1002UT-A

\rightarrow Type:	1002
\rightarrow Package:	TO92UT
\rightarrow Temperature Range:	$T_J = -40 \ ^{\circ}C \ to +170 \ ^{\circ}C$

Hall sensors are available in a wide variety of packaging versions and quantities. For more detailed information, please refer to the brochure: "Hall Sensors: Ordering Codes, Packaging, Handling".

3. Functional Description

3.1. General Function

The HAL1002 is a monolithic integrated circuit which provides a digital output signal. The sensor is based on the HAL83x design.

The Hall plate is sensitive to magnetic north and south polarity. The external magnetic field component perpendicular to the branded side of the package generates a Hall voltage. This voltage is converted to a digital value and processed in the Digital Signal Processing Unit (DSP) according to the settings of the EEPROM registers. The function and the parameters for the DSP are explained in Section 3.2. on page 8.

The setting of the LOCK register disables the programming of the EEPROM memory for all time. This register cannot be reset.

As long as the LOCK register is not set, the output characteristic can be adjusted by programming the EEPROM registers. The IC is addressed by modulating the supply voltage (see Fig. 3–1). After detecting a command, the sensor reads or writes the memory and answers with a digital signal on the output pin. The digital output is switched off during the communication.

Internal temperature compensation circuitry and the choppered offset compensation enable the operation over the full temperature range with minimal changes of the switching points. The circuitry also rejects offset shifts due to mechanical stress from the package. The non-volatile memory consists of redundant EEPROM cells. In addition, the HAL1002 is equipped with devices for overvoltage and reverse-voltage protection at all pins.

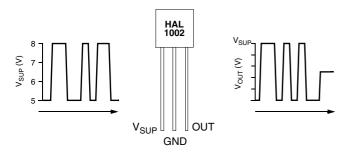
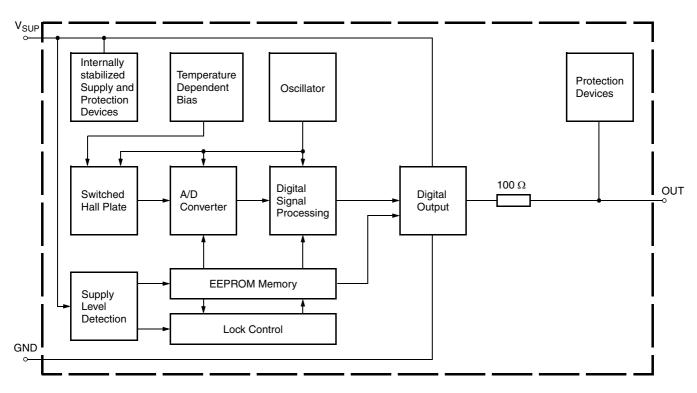
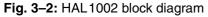
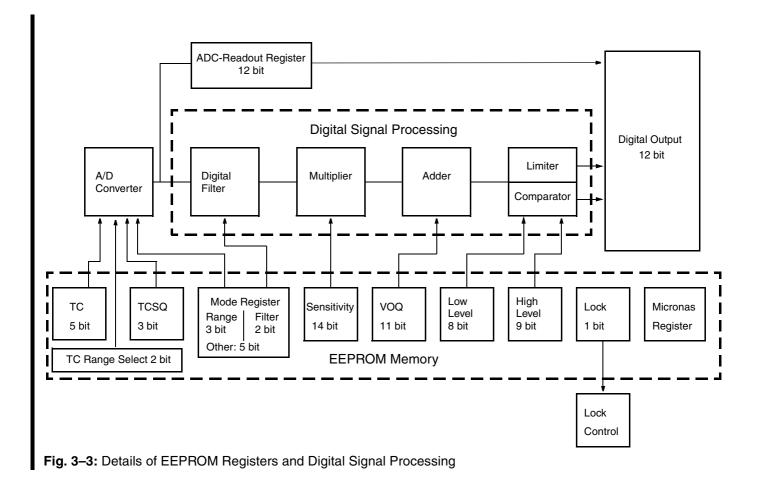


Fig. 3–1: Programming with V_{SUP} modulation







3.2. Digital Signal Processing and EEPROM

The DSP is the main part of the sensor and performs the signal processing. The parameters for the DSP are stored in the EEPROM registers. The details are shown in Fig. 3–3.

Terminology:

SENSITIVITY: name of the register or register value

Sensitivity: name of the parameter

EEPROM Registers:

The EEPROM registers include three groups:

Group 1 contains the registers for the adaption of the sensor to the magnetic system: MODE for selecting the magnetic field range and filter frequency, TC and TCSQ for the temperature characteristics of the magnetic sensitivity and thereby for the switching points.

Group 2 contains the registers for defining the switching points: SENSITIVITY, VOQ, LOW-LEVEL, and HIGH-LEVEL.

The comparator compares the processed signal voltage with the reference values Low-Level and High-Level.

The output switches on (low) if the signal voltage is higher than the High-Level, and switches off (high) if the signal falls below the Low-Level. Several examples of different switching characteristics are shown in Fig. 3–4 to Fig. 3–7.

- The parameter V_{OQ} (Output Quiescent Voltage) corresponds to the signal voltage at B = 0 mT.
- The parameter Sensitivity defines the magnetic sensitivity:

Sensitivity = $\frac{\Delta V_{Signal}}{\Delta B}$

- The signal voltage can be calculated as follows:

 $V_{Signal} \sim Sensitivity \times B + V_{OQ}$

Therefore, the switching points are programmed by setting the SENSITIVITY, VOQ, LOW-LEVEL, and HIGH-LEVEL registers. The available Micronas software calculates the best parameter set respecting the ranges of each register.

Group 3 contains the Micronas registers and LOCK for the locking of all registers. The Micronas registers are programmed and locked during production and are read-only for the customer. These registers are used for oscillator frequency trimming, A/D converter offset compensation, and several other special settings.

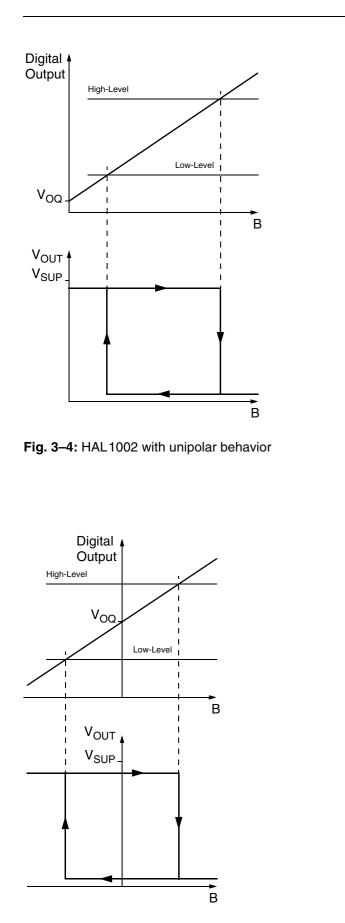


Fig. 3-5: HAL1002 with latching behavior

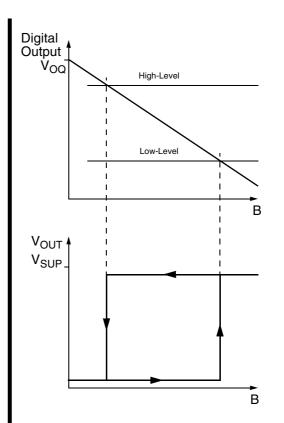
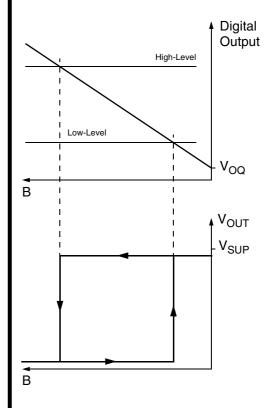
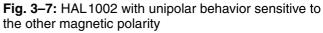


Fig. 3-6: HAL1002 with unipolar inverted behavior





3.3. MODE register

The MODE register contains all bits used to configure the A/D converter and the different output modes.

MODE										
Bit Number	9	8	7	6	5	4	3	2	1	0
Parameter	RANGE	Signed Offset Correction	OUTPUTMODE		FIL	TER	RANG (togeth bit 9)	E er with	Offset Correction	

Table 3-1: MODE register of the HAL 1002

Offset Correction

The Offset Correction function can be used for handling unipolar magnetic fields or systems with high magnetic offset and small magnetic amplitudes. The OFFSET CORRECTION register allows to adjust the digital offset after the built-in A/D-converter. The digital offset can be programmed to 50%, 0% and -50% of A/D-converter full-scale range.

Offset	OFFSET CORRECTION			
Correction	MODE [8]	MODE [0]		
50%	0	1		
0	0	0		
-50%	1	1		

For Offset correction please contact Micronas service.

Magnetic Range

The RANGE bits define the magnetic field range of the A/D converter.

Magnetic Range	RANGE			
	MODE [9]	MODE [2:1]		
15 mT	1	00		
30 mT	0	00		

Table 3-2: Magnetic Range

Magnetic Range	RANGE			
	MODE [9]	MODE [2:1]		
40 mT	1	10		
60 mT	0	01		
80 mT	0	10		
100 mT	0	11		
150 mT	1	11		

Table 3-2: Magnetic Range

Filter

The FILTER bits define the -3 dB frequency of the digital low pass filter.

-3 dB Frequency	MODE [4:3]
80 Hz	00
500 Hz	10
1 kHz	11
2 kHz	01

Output Format

The OUTPUTMODE bits define the different output modes of HAL1002.

Output Format	MODE [7:5]
Switch (positive polarity)	100
Switch (negative polarity)	101

Table 3–3: OUTPUTMODE

TC Register

The temperature dependence of the magnetic sensitivity can be adapted to different magnetic materials in order to compensate for the change of the magnetic strength with temperature. The adaptation is done by programming the тс (Temperature Coefficient) and the TCSQ registers (Quadratic Temperature Coefficient). Thereby, the slope and the curvature of the temperature dependence of the magnetic sensitivity can be matched to the magnet and the sensor assembly. As a result, the output voltage characteristic can be constant over the full temperature range. The sensor can compensate for linear temperature coefficients ranging from about -3100 ppm/K up to 1000 ppm/K and quadratic coefficients from about -7 ppm/K² to 2 ppm/K².

The full TC range is separated in the following four groups:

TC-Range [ppm/k]	GROUP
-3100 to -1800	0
–1750 to –550	2
-500 to +450 (default value)	1
+450 to +1000	3

TC (5 bit) and TCSQ (3 bit) have to be selected individually within each of the four ranges. For example 0 ppm/k requires TC-Range = 1, TC = 15 and TCSQ = 1. Please refer to Section 5.2. on page 20 for more details.

Sensitivity Register

The SENSITIVITY register contains the parameter for the multiplier in the DSP. Sensitivity is programmable between -4 and 4 in steps of 0.00049. Sensitivity = 1 corresponds to an increase of the signal voltage by V_{SUP} if the ADC-READOUT increases by 2048.

VOQ Register

The VOQ register contains the parameter for the adder in the DSP. V_{OQ} is the signal voltage without external magnetic field (B = 0 mT, respectively ADC-READOUT = 0) and programmable from $-V_{SUP}$ up to V_{SUP} For V_{SUP} = 5 V, the register can be changed in steps of 4.9 mV.

Note: If V_{OQ} is programmed to a negative voltage, the maximum signal voltage is limited to:

 $V_{Signal\ max} = V_{OQ} + V_{SUP}$

Reference Level Register

The LOW-LEVEL and HIGH-LEVEL registers contain the reference values of the comparator.

The Low-Level is programmable between 0 V and V_{SUP}/2. The register can be changed in steps of 2.44 mV. The High-Level is programmable between 0 V and V_{SUP} in steps of 2.44 mV.

The four parameters Sensitivity, V_{OQ} , Low-Level, and High-Level define the switching points B_{ON} and B_{OFF} For calibration in the system environment, a 2-point adjustment procedure is recommended (see Section 3.4.). The suitable parameter set for each sensor can be calculated individually by this procedure.

GP Register

This register can be used to store information, like production date or customer serial number. Micronas will store production lot number, wafer number and x,y coordinates in registers GP1 to GP3. The total register contains four blocks with a length of 13 bit each. The customer can read out this information and store it in his production data base for reference or he can store own production information instead.

Note: This register is not a guarantee for traceability because readout of registers is not possible after locking the IC.

To read/write this register it is mandatory to read/write all GP register one after the other starting with GP0. In case of a writing the registers it necessary to first write all registers followed by one store sequence at the end. Even if only GP0 should be changed all other GP registers must first be read and the read out data must be written again to these registers.

LOCK Register

By setting the LSB of this 2-bit register, all registers will be locked, and the sensor will no longer respond to any supply voltage modulation. This bit is active after the first power-off and power-on sequence after setting the LOCK bit. After locking of sensor is active, it will no longer respond to power supply modulation.

Warning: This register cannot be reset!

ADC-READOUT Register

This 14-bit register delivers the actual digital value of the applied magnetic field after filtering but before the signal processing. This register can be read out and is the basis for the calibration procedure of the sensor in the system environment.

D/A-READOUT

This 14-bit register delivers the actual digital value of the applied magnetic field after the signal processing.

This register can be read out and is the basis for the calibration procedure of the sensor in the system environment.

- **Note:** The MSB and LSB are reversed compared with all the other registers. Please reverse this register after readout.
- **Note:** During calibration it is mandatory to select the Analog Output as output format. The D/A-Read-out register can be read out only in the output mode. For all other modes the result read back from the sensor will be a 0. After the calibration the output format can than easily be switched to the wanted output mode.

3.4. General Calibration Procedure

For calibration in the system environment, the application kit from Micronas is recommended. It contains the hardware for the generation of the serial telegram for programming and the corresponding software for the input or calculation of the register values.

In this section, the programming of the sensor using this tool is explained. Please refer to Section 5. on page 24 for information about programming without this tool. For the individual calibration of each sensor in the customer's application, a two-point adjustment is recommended (see Fig. 3–1 for an example). When using the application kit, the calibration can be done in three steps:

Step 1: Input of the registers which need not be adjusted individually

The magnetic circuit, the magnetic material with its temperature characteristics, and the filter frequency, are given for this application.

Therefore, the values of the following registers should be identical for all sensors in the application.

- FILTER (according to maximum signal frequency) The 500 Hz range is recommended for highest accuracy.
- RANGE (according to the maximum magnetic field at the sensor position)
- TC and TCSQ (depends on the material of the magnet and the other temperature dependencies of the application)

Write the appropriate settings into the HAL1002 registers.

Step 2: Calculation of the Sensor Parameters

Fig. 3–1 shows the typical characteristics for a contactless switch. There is a mechanical range where the sensor must be switched high and where the sensor must be switched low.

Set the system to the calibration point where the sensor output must be high, and press the key "Readout B_{OFF} ". The result is the corresponding ADC-READOUT value.

Note: The magnetic south pole on the branded side generates negative ADC-READOUT values, the north polarity positive values.

Then, set the system to the calibration point where the sensor output must be low, press the key "Readout B_{ON} " and get the second ADC-READOUT value.

Now, adjust the hysteresis to the desired value. The hysteresis is the difference between the switching points and suppresses oscillation of the output signal. With 100% hysteresis, the sensor will switch low and high exactly at the calibration points. A lower value will adjust the switching points closer together. Fig. 3–1 shows an example with 80% hysteresis.

By pressing the key "calibrate and store", the software will calculate the corresponding parameters for Sensitivity, VOQ, Low-Level, High-Level and stores these values in the EEPROM.

This calibration must be done individually for each sensor.

The sensor is now calibrated for the customer application. However, the programming can be changed again and again if necessary.

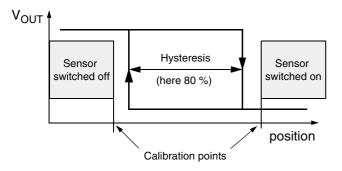


Fig. 3-1: Characteristics of a position switch

Step 3: Locking the Sensor

The last step is activating the LOCK function with the "lock" key. The sensor is now locked and does not respond to any programming or reading commands.

Warning: The LOCK register cannot be reset!

3.5. Example: Calibration of a Position Switch

The following description explains the calibration procedure using a position switch as an example:

- The mechanical switching points are given.
- temperature coefficient of the magnet: -500 ppm/K

Step 1: Input of the registers which need not be adjusted individually

The register values for the following registers are given for all sensors in the application:

- FILTER Select the filter frequency: 500 Hz
- RANGE Select the magnetic field range: 30 mT
- TC
 For this magnetic material: 6
- TCSQ For this magnetic material: 14

Enter these values in the software and use the "write and store" command to store these values permanently in the registers.

Step 2: Calculation of the Sensor Parameters

Set the system to the calibration point where the sensor output must be high and press "Readout B_{OFF} ".

Set the system to the calibration point where the sensor output must be low and press "Readout B_{ON} ".

Now, adjust the hysteresis to 80% and press the key "calibrate and store".

Step 3: Locking the Sensor

The last step is activating the LOCK function with the "LOCK" command. The sensor is now locked and does not respond to any programming or reading commands. Please note that the LOCK function becomes effective after power-down and power-up of the Hall-IC.

Warning: The LOCK register cannot be reset!

4. Specifications

4.1. Outline Dimensions

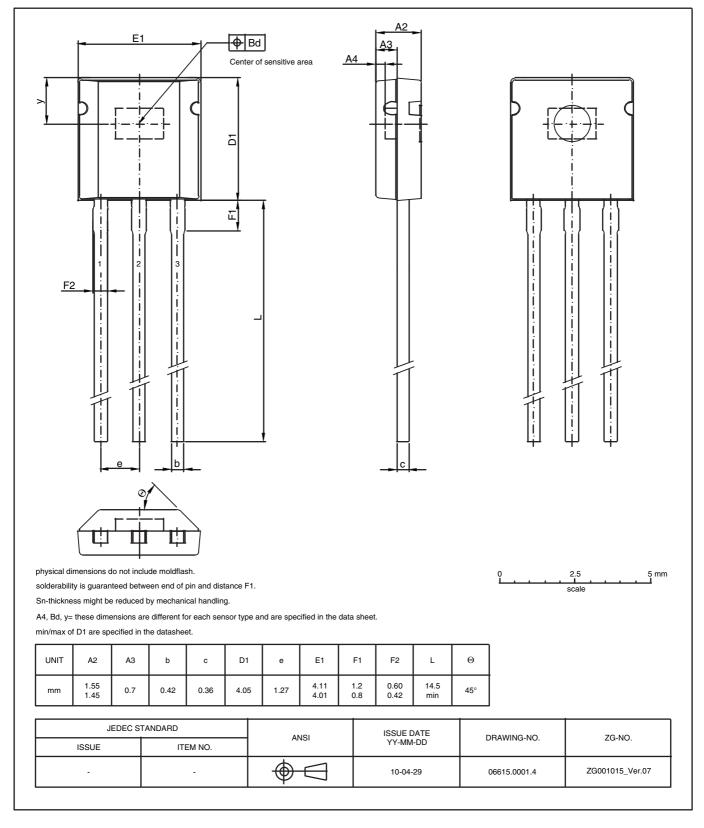


Fig. 4–1:

TO92UT-2 Plastic Transistor Standard UT package, 3 leads Weight approximately 0.12 g

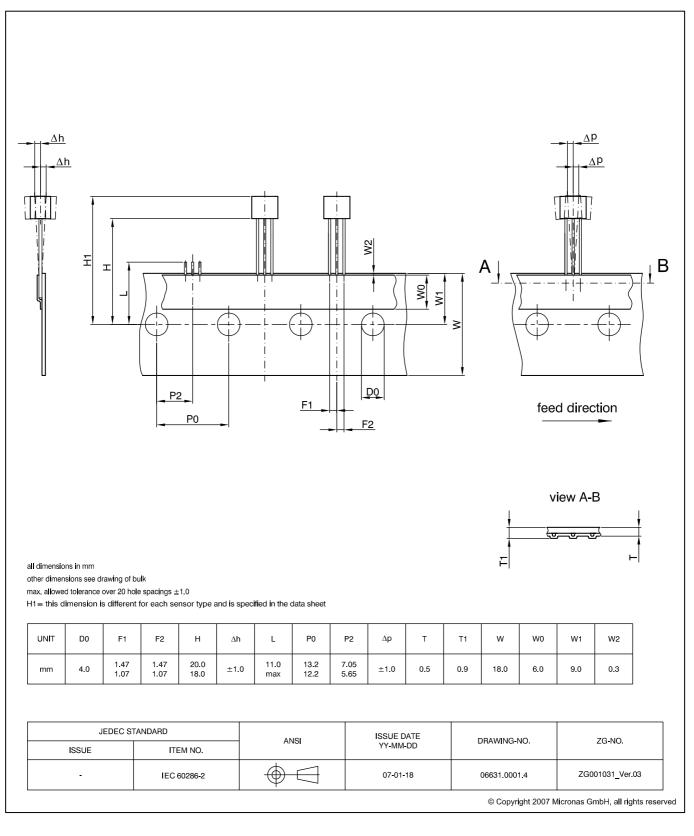


Fig. 4–2:

TO92UA/UT: Dimensions ammopack inline, not spread

4.2. Soldering, Welding and Assembly

Please check the Micronas Document "Guidelines for the Assembly of HAL Packages" for further information about solderability, welding, assembly, and second-level packaging. The document is available on the Micronas website or on the service portal.

4.3. Pin Connections and Short Descriptions

Pin No.	Pin Name	Short Description
1	V _{SUP}	Supply Voltage and Programming Pin
2	GND	Ground
3	OUT	Push-Pull Output and Selection Pin

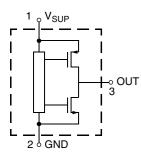


Fig. 4–3: Pin configuration

4.4. Dimension of Sensitive Area

0.25 mm x 0.25 mm

4.5. Physical Dimensions

	TO92UT-1/-2
A4	0.3 mm nominal
Bd	0.3 mm
D1	4.05 mm ± 0.05 mm
H1	min. 22.0 mm max. 24.1 mm
у	1.5 mm nominal

4.6. Absolute Maximum Ratings

Stresses beyond those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these conditions is not implied. Exposure to absolute maximum rating conditions for extended periods will affect device reliability.

This device contains circuitry to protect the inputs and outputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than absolute maximum-rated voltages to this circuit.

Symbol	Parameter	Pin No.	Min.	Max.	Unit	Condition	
V _{SUP}	Supply Voltage	1	-8.5	11	V	t < 96 h ³⁾	
V _{SUP}	Supply Voltage	1	-16	16	V	t < 1 h ³⁾	
V _{OUT}	Output Voltage	3	-5	16	V		
V _{OUT} – V _{SUP}	Excess of Output Voltage over Supply Voltage	3,1	_	2	V		
I _{OUT}	Continuous Output Current	3	-10	10	mA		
t _{Sh}	Output Short Circuit Duration	3	_	10	min		
V _{ESD}	ESD Protection ¹⁾	1 3	-8.0 -7.5	8.0 7.5	kV		
TJ	Junction Temperature under bias ²⁾		-50	190	°C		
 ¹⁾ AEC-Q100-002 (100 pF and 1.5 kΩ) ²⁾ For 96 h - Please contact Micronas for other temperature requirements ³⁾ No cumulated stress 							

All voltages listed are referenced to ground (GND).

4.6.1. Storage and Shelf Life

The permissible storage time (shelf life) of the sensors is unlimited, provided the sensors are stored at a maximum of 30 °C and a maximum of 85% relative humidity. At these conditions, no Dry Pack is required.

Solderability is guaranteed for two years from the date code on the package.

4.7. Recommended Operating Conditions

Functional operation of the device beyond those indicated in the "Recommended Operating Conditions/Characteristics" is not implied and may result in unpredictable behavior, reduce reliability and lifetime of the device.

All voltages listed are referenced to ground (GND).

Symbol	Parameter	Pin No.	Min.	Тур.	Max.	Unit	Condition
V _{SUP}	Supply Voltage	1	4.5	5	8.5	V	
I _{OUT}	Continuous Output Current	3	-1.2	_	1.2	mA	
RL	Load Resistor	3	5.0	10	_	kΩ	Can be pull-up or pull- down resistor (analog output only)
CL	Load Capacitance	3	0.33	100	1000	nF	
N _{PRG}	Number of EEPROM Pro- gramming Cycles	-	_	_	100	cycles	0°C < T _{amb} < 55°C
TJ	Junction Temperature Range ¹⁾	_	-40 -40 -40	_ _ _	125 150 170	°C °C °C	for 8000 h ²⁾ for 2000 h ²⁾ for 1000 h ²⁾
 ¹⁾ Depends on the temperature profile of the application. Please contact Micronas for life time calculations. ²⁾ Time values are not cumulative 							

4.8. Characteristics

at $T_J = -40$ °C to +170 °C, $V_{SUP} = 4.5$ V to 8.5 V, after programming and locking of the device, at Recommended Operation Conditions if not otherwise specified in the column "Conditions". Typical Characteristics for $T_J = 25$ °C and $V_{SUP} = 5$ V.

Symbol	Parameter	Pin No.	Min.	Тур.	Max.	Unit	Conditions
I _{DD}	Supply Current over Temperature Range	1		7	10	mA	
V _{OUTH}	Output High Voltage	3	4.65	4.8		V	V_{SUP} = 5 V, $-1~\text{mA} \leq I_{OUT} \leq 1~\text{mA}$
V _{OUTL}	Output Low Voltage	3		0.2	0.35	V	V_{SUP} = 5 V, $-1~\text{mA} \leq I_{OUT} \leq 1~\text{mA}$
f _{ADC}	Internal ADC Frequency	-	120	128	140	kHz	$T_J = 25 \ ^{\circ}C$
f _{ADC}	Internal ADC Frequency over Temperature Range	_	110	128	150	kHz	V _{SUP} = 5 V
t _{r(O)}	Response Time of Output	3	_	5 4 2 1	10 8 4 2	ms ms ms ms	3 dB Filter frequency = 80 Hz 3 dB Filter frequency = 160 Hz 3 dB Filter frequency = 500 Hz 3 dB Filter frequency = 2 kHz C_L = 10 nF, time from 10% to 90% of final output voltage for a steplike signal B _{step} from 0 mT to B _{max}
t _{d(O)}	Delay Time of Output	3		0.1	0.5	ms	C _L = 10 nF
t _{POD}	Power-Up Time (Time to reach stabilized Output Voltage)			6 5 3 2	11 9 5 3	ms ms ms ms	3 dB Filter frequency = 80 Hz 3 dB Filter frequency = 160 Hz 3 dB Filter frequency = 500 Hz 3 dB Filter frequency = 2 kHz C_L = 10 nF, 90% of V _{OUT}
BW	Small Signal Bandwidth (–3 dB)	3	_	2	_	kHz	B _{AC} < 10 mT; 3 dB Filter frequency = 2 kHz
R _{thja} R _{thjc} R _{thjs}	Thermal Resistance Junction to Ambient Junction to Case Junction to Solder Point				235 61 159	K/W	measured on a 1s0p board measured on a 1s0p board measured on a 1s1p board
B _{ON_OFF_res}	Programming Resolution			12		bit	including sign bit
B _{ON_OFF_acc}	Threshold Accuracy		-0.1		+0.1	%	at $T_J = 25 \ ^{\circ}C$ based on characterization
B _{ON_OFF_acc}	Threshold Accuracy		-4		+4	%	over operating temperature range based on characterization

4.9. Magnetic Characteristics

at $T_J = -40$ °C to +170 °C, $V_{SUP} = 4.5$ V to 8.5 V, GND = 0 V after programming and locking, at Recommended Operation Conditions if not otherwise specified in the column "Conditions". Typical Characteristics for $T_J = 25$ °C and $V_{SUP} = 5$ V.

Symbol	Parameter	Pin No.	Min.	Тур.	Max.	Unit	Test Conditions
B _{Offset}	Magnetic Offset	3	-0.5	0	0.5	mT	B = 0 mT, I_{OUT} = 0 mA, T_J = 25 °C, unadjusted sensor
ΔB _{Offset}	Magnetic Offset Drift		-200	0	200	μΤ	$B = 0 \text{ mT, } I_{OUT} = 0 \text{ mA}$ $V_{SUP} = 5 \text{ V; } 60 \text{ mT range, } 3db$ frequency = 500 Hz, TC = 15, TCSQ = 1, TC-Range = 1 -0.65 < sensitivity < 0.65

5. Application Notes

5.1. Application Circuit

For EMC protection, it is recommended to connect one ceramic 100 nF capacitor between ground and the supply voltage, and between ground and the output pin.

Please note that during programming, the sensor will be supplied repeatedly with the programming voltage of 12.5 V for 100 ms. All components connected to the V_{SUP} line at this time must be able to resist this voltage.

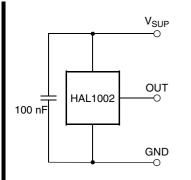


Fig. 5-1: Recommended application circuit

For application circuits for high supply voltages, such as 24 V, please contact the Micronas application service.

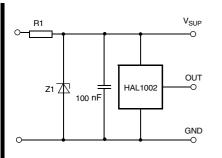


Fig. 5–2: Example for an application circuit for high supply voltage

5.2. Temperature Compensation

The relationship between the temperature coefficient of the magnet and the corresponding TC and TCSQ codes for linear compensation is given in the following table. In addition to the linear change of the magnetic field with temperature, the curvature can be adjusted as well. For this purpose, other TC and TCSQ combinations are required which are not shown in the table. Please contact Micronas for more detailed information on this higher order temperature compensation.

The HAL83x and HAL1002 contain the same temperature compensation circuits. If an optimal setting for the HAL83x is already available, the same settings may be used for the HAL1002.

Temperature Coefficient of Magnet (ppm/K)	TC-Range	тс	TCSQ
1075	3	31	7
1000	3	28	1
900	3	24	0
750	3	16	2
675	3	12	2
575	3	8	2
450	3	4	2
400	1	31	0
250	1	24	1
150	1	20	1
50	1	16	2
0	1	15	1
-100	1	12	0
-200	1	8	1
-300	1	4	4
-400	1	0	7
-500	1	0	0
-600	2	31	2
-700	2	28	1
-800	2	24	3
-900	2	20	6
-1000	2	16	7

Temperature Coefficient of Magnet (ppm/K)	TC-Range	тс	TCSQ
-1100	2	16	2
-1200	2	12	5
-1300	2	12	0
-1400	2	8	3
-1500	2	4	7
-1600	2	4	1
-1700	2	0	6
-1800	0	31	6
-1900	0	28	7
-2000	0	28	2
-2100	0	24	6
-2200	0	24	1
-2400	0	20	0
-2500	0	16	5
-2600	0	14	5
-2800	0	12	1
-2900	0	8	6
-3000	0	8	3
-3100	0	4	7
-3300	0	4	1
-3500	0	0	4

Note: The above table shows only some approximate values. Micronas recommends to use the TC-Calc software to find optimal settings for temperature coefficients. Please contact Micronas for more detailed information.

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature T_J) is higher than the temperature outside the package (ambient temperature T_A).

$$T_J = T_A + \Delta T$$

At static conditions and continuous operation, the following equation applies:

$$\Delta T = I_{SUP} \times V_{SUP} \times R_{thI}$$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for I_{SUP} and R_{th} , and the max. value for V_{SUP} from the application.

For V_{SUP} = 5.5 V, R_{th} = 235 K/W, and I_{SUP} = 10 mA, the temperature difference ΔT = 12.93 K.

For all sensors, the junction temperature $T_{\rm J}$ is specified. The maximum ambient temperature $T_{\rm Amax}$ can be calculated as:

$$T_{Amax} = T_{Imax} - \Delta T$$

5.4. EMC and ESD

Please contact Micronas for the detailed investigation reports with the EMC and ESD results.

6. Programming

6.1. Definition of Programming Pulses

The sensor is addressed by modulating a serial telegram on the supply voltage. The sensor answers with a serial telegram on the output pin.

The bits in the serial telegram have a different bit time for the V_{SUP}-line and the output. The bit time for the V_{SUP}-line is defined through the length of the Sync Bit at the beginning of each telegram. The bit time for the output is defined through the Acknowledge Bit.

A logical "0" is coded as no voltage change within the bit time. A logical "1" is coded as a voltage change between 50% and 80% of the bit time. After each bit, a voltage change occurs.

6.2. Definition of the Telegram

Each telegram starts with the Sync Bit (logical 0), 3 bits for the Command (COM), the Command Parity Bit (CP), 4 bits for the Address (ADR), and the Address Parity Bit (AP).

There are 4 kinds of telegrams:

- Write a register (see Fig. 6-2)
- After the AP Bit, follow 14 Data Bits (DAT) and the Data Parity Bit (DP). If the telegram is valid and the command has been processed, the sensor answers with an Acknowledge Bit (logical 0) on the output.
- Read a register (see Fig. 6–3)
 After evaluating this command, the sensor answers with the Acknowledge Bit, 14 Data Bits, and the Data Parity Bit on the output.
- Programming the EEPROM cells (see Fig. 6–4) After evaluating this command, the sensor answers with the Acknowledge Bit. After the delay time t_w, the supply voltage rises up to the programming voltage.
- Activate a sensor (see Fig. 6–5) If more than one sensor is connected to the supply line, selection can be done by first deactivating all sensors. The output of all sensors have to be pulled to ground. With an Activate pulse on the appropriate output pin, an individual sensor can be selected. All following commands will only be accepted from the activated sensor.

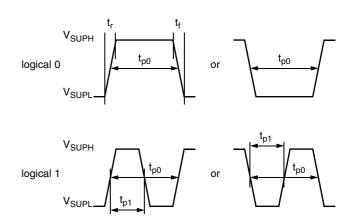
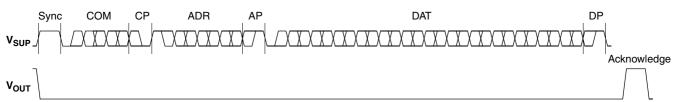


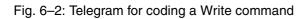
Fig. 6-1: Definition of logical 0 and 1 bit

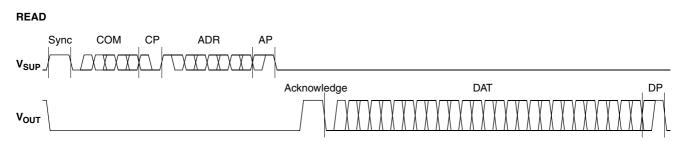
Table 6–1: Telegram parameters

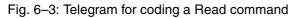
Symbol	Parameter	Pin	Min.	Тур.	Max.	Unit	Remarks
V _{SUPL}	Supply Voltage for Low Level during Programming	1	5	5.6	6	V	
V _{SUPH}	Supply Voltage for High Level during Programming	1	6.8	8.0	8.5	V	
t _r	Rise time	1	-	-	0.05	ms	
t _f	Fall time	1	_	_	0.05	ms	
t _{p0}	Bit time on V _{SUP}	1	1.7	1.75	1.9	ms	t_{p0} is defined through the Sync Bit
t _{pOUT}	Bit time on output pin	3	2	3	4	ms	t _{pOUT} is defined through the Acknowledge Bit
t _{p1}	Duty-Cycle Change for logical 1	1, 3	50	65	80	%	% of t _{p0} or t _{pOUT}
V _{SUPPROG}	Supply Voltage for Programming the EEPROM	1	12.4	12.5	12.6	V	
t _{PROG}	Programming Time for EEPROM	1	95	100	105	ms	
t _{rp}	Rise time of programming voltage	1	0.2	0.5	1	ms	
t _{fp}	Fall time of programming voltage	1	0	-	1	ms	
t _w	Delay time of programming voltage after Acknowledge	1	0.5	0.7	1	ms	
V _{act}	Voltage for an Activate pulse	3	3	4	5	V	
t _{act}	Duration of an Activate pulse	3	0.05	0.1	0.2	ms	
Vout,deact	Output voltage after deactivate command	3	0	0.1	0.2	V	

WRITE









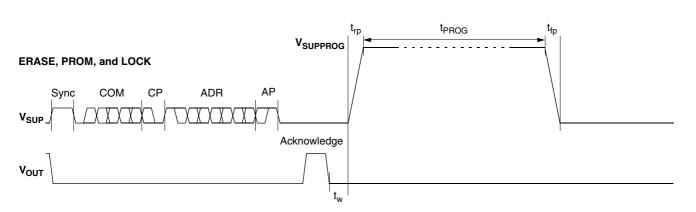


Fig. 6-4: Telegram for coding the EEPROM programming

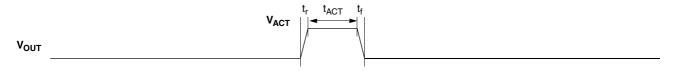


Fig. 6–5: Activate pulse

6.3. Telegram Codes

Sync Bit

Each telegram starts with the Sync Bit. This logical "0" pulse defines the exact timing for t_{p0} .

Command Bits (COM)

The Command code contains 3 bits and is a binary number. Table 6–2 shows the available commands and the corresponding codes for the HAL 1002.

Command Parity Bit (CP)

This parity bit is "1" if the number of zeros within the 3 Command Bits is uneven. The parity bit is "0", if the number of zeros is even.

Address Bits (ADR)

The Address code contains 4 bits and is a binary number. Table 6–3 shows the available addresses for the HAL 1002 registers.

Address Parity Bit (AP)

This parity bit is "1" if the number of zeros within the 4 Address bits is uneven. The parity bit is "0" if the number of zeros is even.

Data Bits (DAT)

The 14 Data Bits contain the register information.

The registers use different number formats for the Data Bits. These formats are explained in Section 6.4.

In the Write command, the last bits are valid. If, for example, the TC register (10 bits) is written, only the last 10 bits are valid.

In the Read command, the first bits are valid. If, for example, the TC register (10 bits) is read, only the first 10 bits are valid.

Data Parity Bit (DP)

This parity bit is "1" if the number of zeros within the binary number is even. The parity bit is "0" if the number of zeros is uneven.

Acknowledge

After each telegram, the output answers with the Acknowledge signal. This logical "0" pulse defines the exact timing for $t_{\rm pOUT}$.

Table 6–2: Available commands

Command	Code	Explanation
READ	2	read a register
WRITE	3	write a register
PROM	4	program all nonvolatile registers (except the lock bits)
ERASE	5	erase all nonvolatile registers (except the lock bits)

6.4. Number Formats

Binary number:

The most significant bit is given as first, the least significant bit as last digit.

Example: 101001 represents 41 decimal.

Signed binary number:

The first digit represents the sign of the following binary number (1 for negative, 0 for positive sign).

Example: 0101001 represents +41 decimal 1101001 represents -41 decimal

Two's-complement number:

The first digit of positive numbers is "0", the rest of the number is a binary number. Negative numbers start with "1". In order to calculate the absolute value of the number, calculate the complement of the remaining digits and add "1".

Example:	0101001	represents +41	decimal
-	1010111	represents -41	decimal

6.5. Register Information

LOW Level

- The register range is from 0 up to 255.
- The register value is calculated by:

$$LOW Level = \frac{Low-Level Voltage \times 2}{V_{SUP}} \times 255$$

HIGH Level

- The register range is from 0 up to 511.
- The register value is calculated by:

HIGH Level =
$$\frac{\text{High-Level Voltage}}{V_{SUP}} \times 511$$

VOQ

- The register range is from -1024 up to 1023.
- The register value is calculated by:

$$VOQ = \frac{V_{OQ}}{V_{SUP}} \times 1024$$